2SD669AD

Rev.E May.-2016

DATA SHEET

/ Descriptions

WR0585 Ṃ Ṃ Ŀ QSQ Æ Ṁ ɥ s ǁ ˥ Silicon NPN transistor in a TO-252 Plastic Package.

/ Features

љ 5VE97<DG Ӣ ´

Complementary pair with 2SB649AD.

/ Applications

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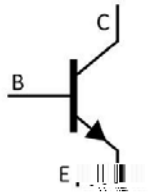
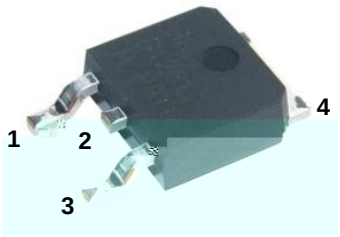
Low frequency power amplifier.

/ Equivalent Circuit



/ Pinning



PIN1 χ Base PIN 2,4 χ Collector PIN 3 χ Emitter

/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	B	C	D
h_{FE} Range	60 120	100 200	160 320

v ̈Ω̣ Parameter	ɬ N Symbol	̈Ω̣Ö Rating	D Ḫ Unit
Collector to Base Voltage	V_{CBO}	180	V
Collector to Emitter Voltage	V_{CEO}	160	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	1.5	A
Collector Current – Continuous(Pulse)	I_{CP}	3.0	A
Collector Power Dissipation	P_C	1.0	W
Collector Power Dissipation	P_C(Tc=25)	10	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

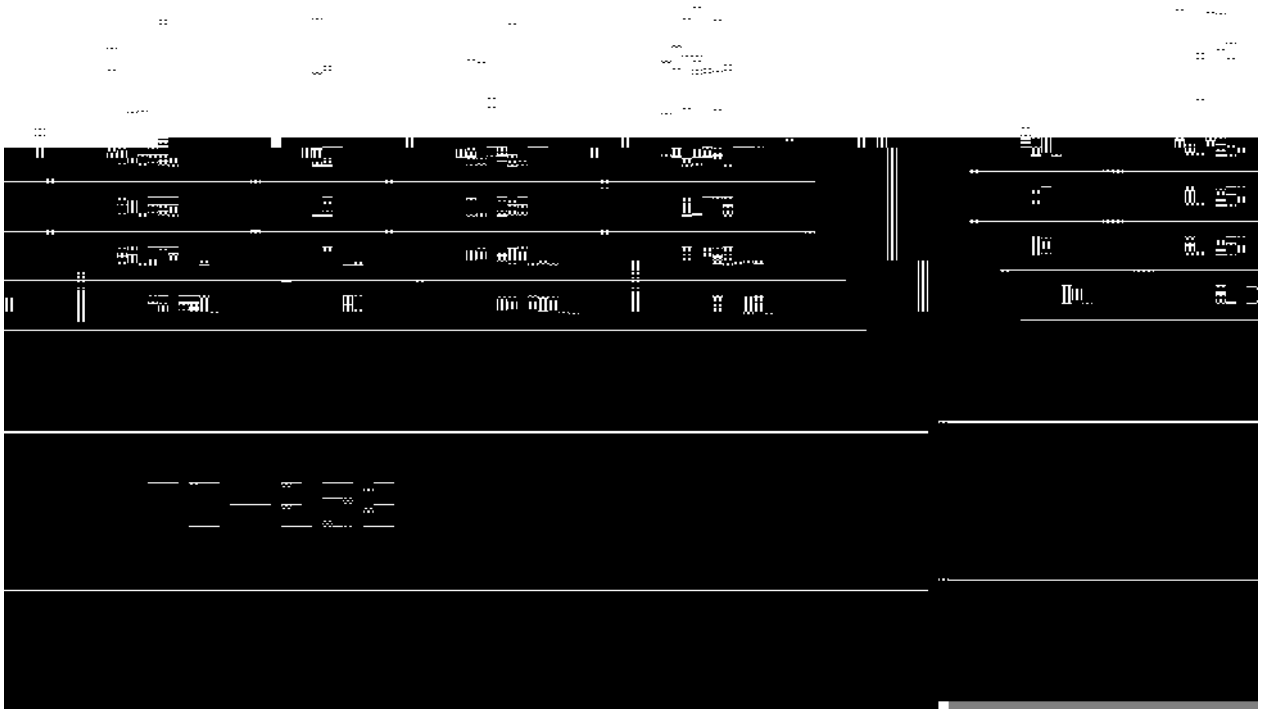
v ̈Ω̣ Parameter	ɬ N Symbol	⊥⊥ ;ɬ Ţ Test Conditions	ω̣ ṇ Ö Min	Ɛ ʒ Ö Typ	ω̣ ʑ Ö Max	D Ḫ Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=1.0mA I_E=0	180			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=10mA R_{BE}=∞	160			V
Emitter to Base Breakdown Voltage	V_{EBO}	I				

/ Electrical Characteristic Curve

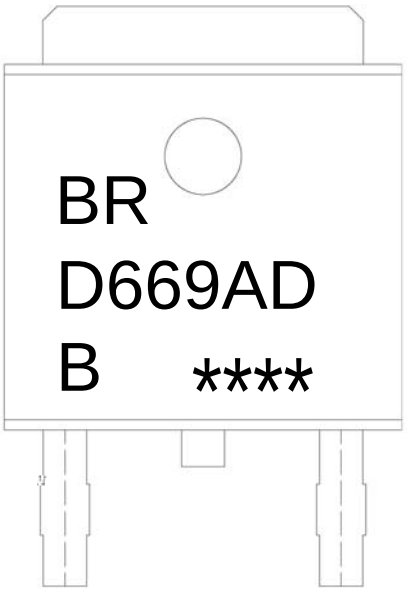


/ Package Dimensions





/ Marking Instructions



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G99<DG χ	⌘ ⅔ ᴺ Ɱ
E=	⌘ h_{FE} ʿ ⁶ Ɱ
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Note:

BR:	Company Code
D669AD:	Product Type.
B:	h_{FE} Classifications Symbol
****:	Lot No. Code, code change with Lot No.

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